

### General Description

These N-channel MOSFET are produced using advanced MagnaChip's MOSFET Technology, which provides low on-state resistance, high switching performance and excellent quality.

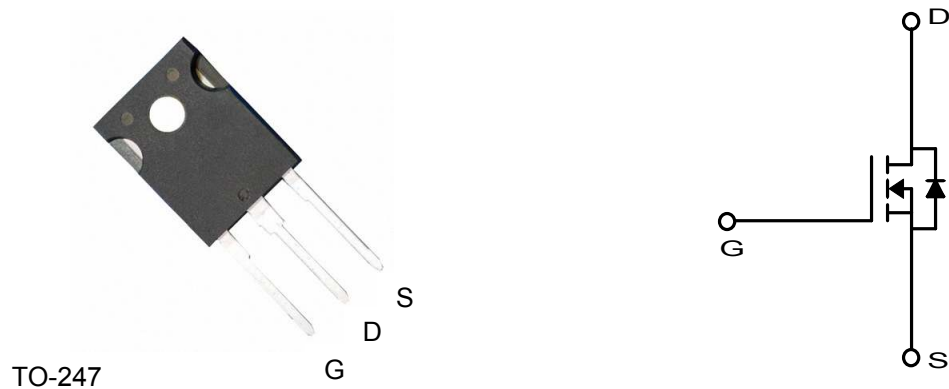
These devices are suitable device for SMPS, high Speed switching and general purpose applications.

### Features

- $V_{DS} = 500V$
- $I_D = 23.0A$  @  $V_{GS} = 10V$
- $R_{DS(ON)} \leq 0.245\Omega$  @  $V_{GS} = 10V$

### Applications

- Power Supply
- HID
- Lighting



### Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Drain-Source Voltage		$V_{DSS}$	500	V
Gate-Source Voltage		$V_{GSS}$	±30	V
Continuous Drain Current	$T_C=25^\circ C$	$I_D$	23	A
	$T_C=100^\circ C$		14.6	A
Pulsed Drain Current <sup>(1)</sup>		$I_{DM}$	92	A
Power Dissipation	$T_C=25^\circ C$	$P_D$	290	W
	Derate above 25 °C		2.33	W/°C
Repetitive Avalanche Energy <sup>(1)</sup>		$E_{AR}$	29	mJ
Peak Diode Recovery $dv/dt$ <sup>(3)</sup>		$dv/dt$	4.5	V/ns
Single Pulse Avalanche Energy <sup>(4)</sup>		$E_{AS}$	950	mJ
Junction and Storage Temperature Range		$T_J, T_{stg}$	-55~150	°C

\*  $I_D$  limited by maximum junction temperature

### Thermal Characteristics

Characteristics	Symbol	Rating	Unit
Thermal Resistance, Junction-to-Ambient <sup>(1)</sup>	$R_{\theta JA}$	40	°C/W
Thermal Resistance, Junction-to-Case <sup>(1)</sup>	$R_{\theta JC}$	0.44	

## Ordering Information

Part Number	Temp. Range	Package	Packing	RoHS Status
MDQ23N50DTP	-55~150°C	TO-247	Tube	Pb Free

## Electrical Characteristics (Ta =25°C)

Characteristics	Symbol	Test Condition	Min	Typ	Max	Unit
<b>Static Characteristics</b>						
Drain-Source Breakdown Voltage	$BV_{DSS}$	$I_D = 250\mu A, V_{GS} = 0V$	500	-	-	V
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2.0	-	4.0	
Drain Cut-Off Current	$I_{DSS}$	$V_{DS} = 500V, V_{GS} = 0V$	-	-	1	$\mu A$
Gate Leakage Current	$I_{GSS}$	$V_{GS} = \pm 30V, V_{DS} = 0V$	-	-	100	nA
Drain-Source ON Resistance	$R_{DS(ON)}$	$V_{GS} = 10V, I_D = 11.5A$	-	0.2	0.245	$\Omega$
Forward Transconductance	$g_{fs}$	$V_{DS} = 30V, I_D = 11.5A$	-	13	-	S

## Dynamic Characteristics

Total Gate Charge	$Q_g$	$V_{DS} = 400V, I_D = 23A, V_{GS} = 10V$	-	76	-	nC
Gate-Source Charge	$Q_{gs}$		-	16	-	
Gate-Drain Charge	$Q_{gd}$		-	20	-	
Input Capacitance	$C_{iss}$	$V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$	-	3280	-	pF
Reverse Transfer Capacitance	$C_{rss}$		-	23	-	
Output Capacitance	$C_{oss}$		-	325	-	
Turn-On Delay Time	$t_{d(on)}$	$V_{GS} = 10V, V_{DS} = 250V, I_D = 23A, R_G = 25\Omega$	-	50	-	ns
Rise Time	$t_r$		-	155	-	
Turn-Off Delay Time	$t_{d(off)}$		-	230	-	
Fall Time	$t_f$		-	195	-	

## Drain-Source Body Diode Characteristics

Maximum Continuous Drain to Source Diode Forward Current	$I_S$		-	-	23	A
Source-Drain Diode Forward Voltage	$V_{SD}$	$I_S = 23A, V_{GS} = 0V$	-	-	1.4	V
Body Diode Reverse Recovery Time	$t_{rr}$	$I_F = 23A, di/dt = 100A/\mu s^{(3)}$	-	450	-	ns
Body Diode Reverse Recovery Charge	$Q_{rr}$		-	6	-	$\mu C$

Notes :

1. Pulse width is based on  $R_{\theta JC}$  &  $R_{\theta JA}$  and the maximum allowed junction temperature of 150°C.
2. Pulse test: pulse width  $\leq 300\mu s$ , duty cycle  $\leq 2\%$ , pulse width limited by junction temperature  $T_{J(MAX)} = 150^\circ C$ .
3.  $I_{SD} \leq 23A$ ,  $di/dt \leq 200A/\mu s$ ,  $V_{DD} \leq BV_{dss}$ ,  $R_g = 25\Omega$ , Starting  $T_J = 25^\circ C$
4.  $L = 3.24mH$ ,  $I_{AS} = 23A$ ,  $V_{DD} = 50V$ ,  $R_g = 25\Omega$ , Starting  $T_J = 25^\circ C$

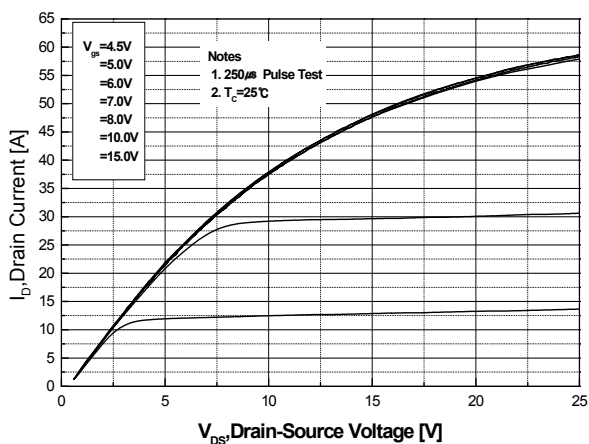


Fig.1 On-Region Characteristics

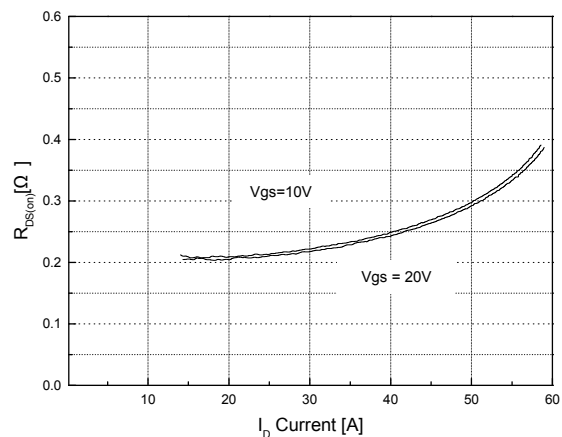


Fig.2 On-Resistance Variation with Drain Current and Gate Voltage

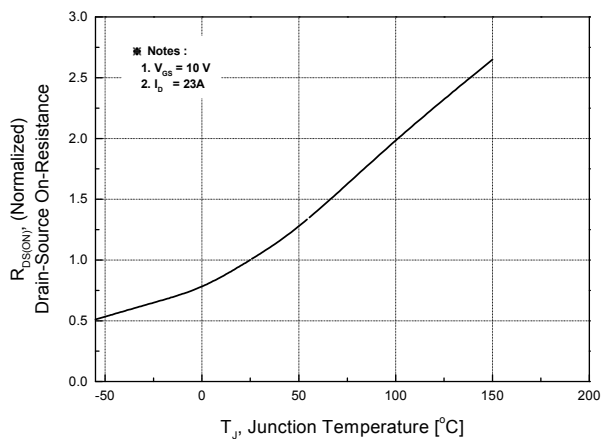


Fig.3 On-Resistance Variation with Temperature

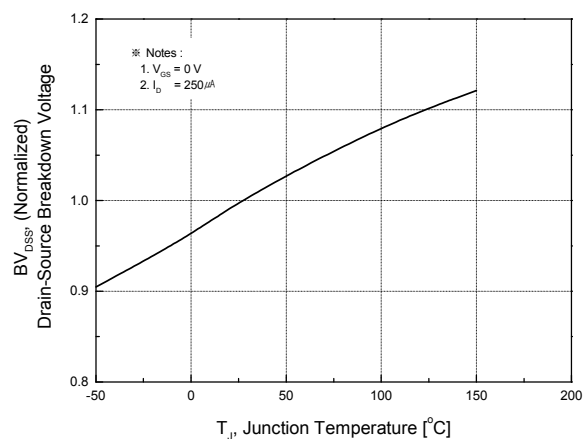


Fig.4 Breakdown Voltage Variation vs. Temperature

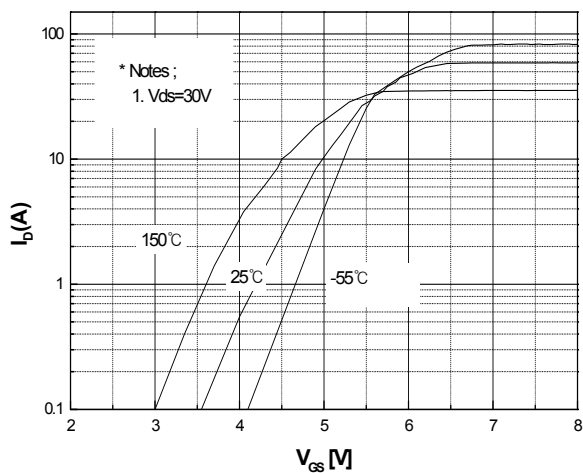


Fig.5 Transfer Characteristics

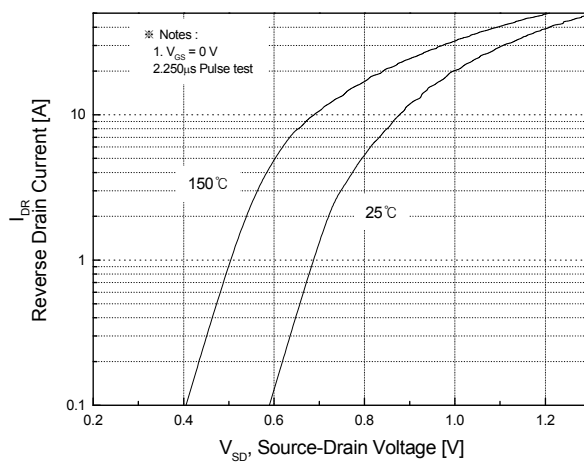


Fig.6 Body Diode Forward Voltage Variation with Source Current and Temperature

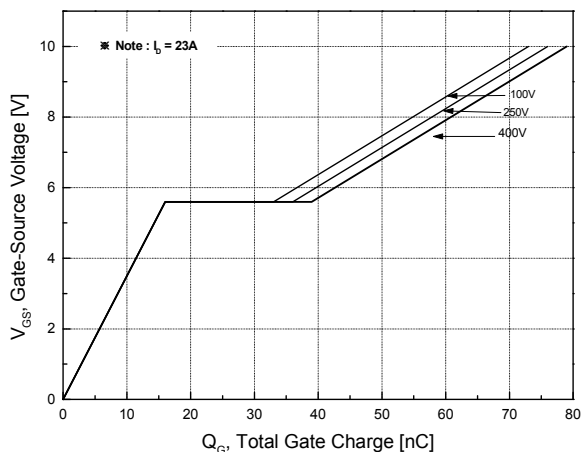


Fig.7 Gate Charge Characteristics

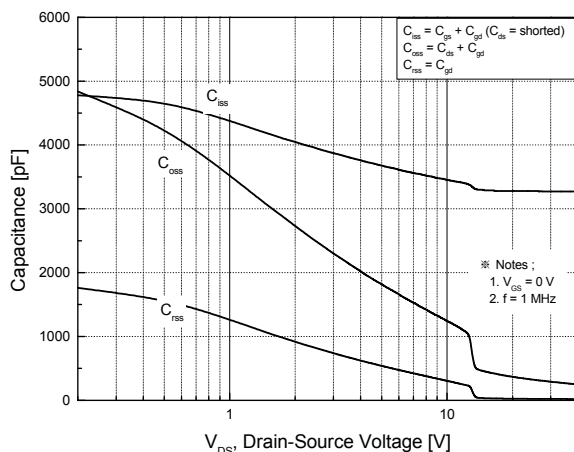


Fig.8 Capacitance Characteristics

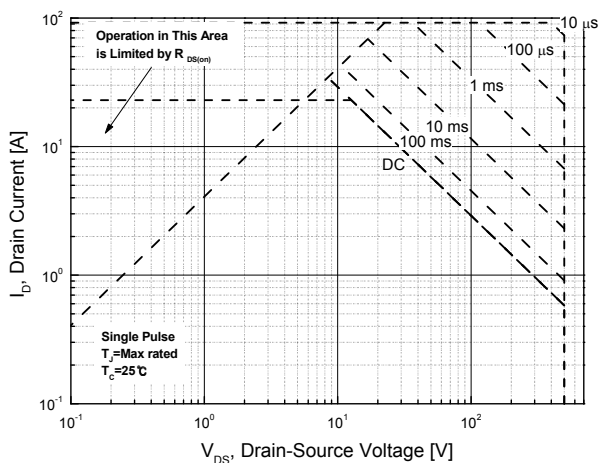


Fig.9 Maximum Safe Operating Area

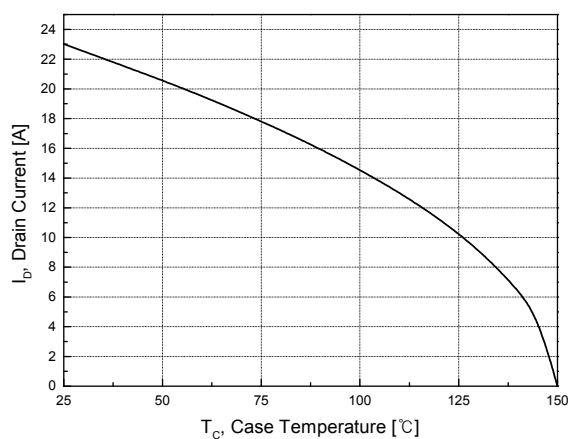


Fig.10 Maximum Drain Current vs. Case Temperature

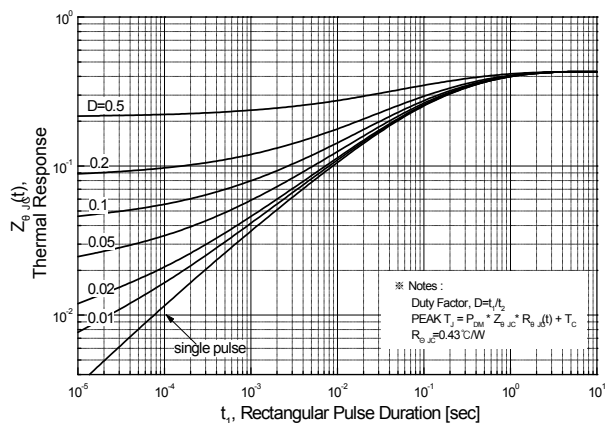


Fig.11 Transient Thermal Response Curve

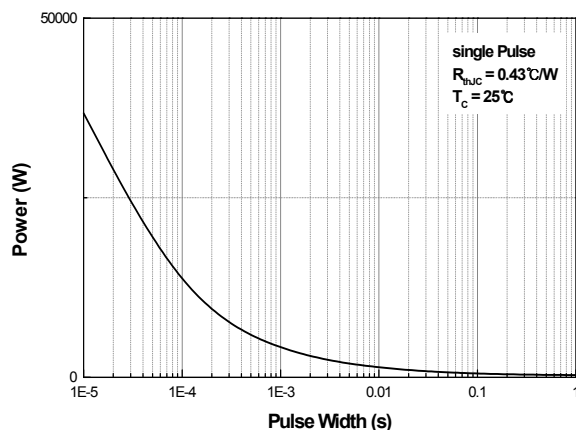
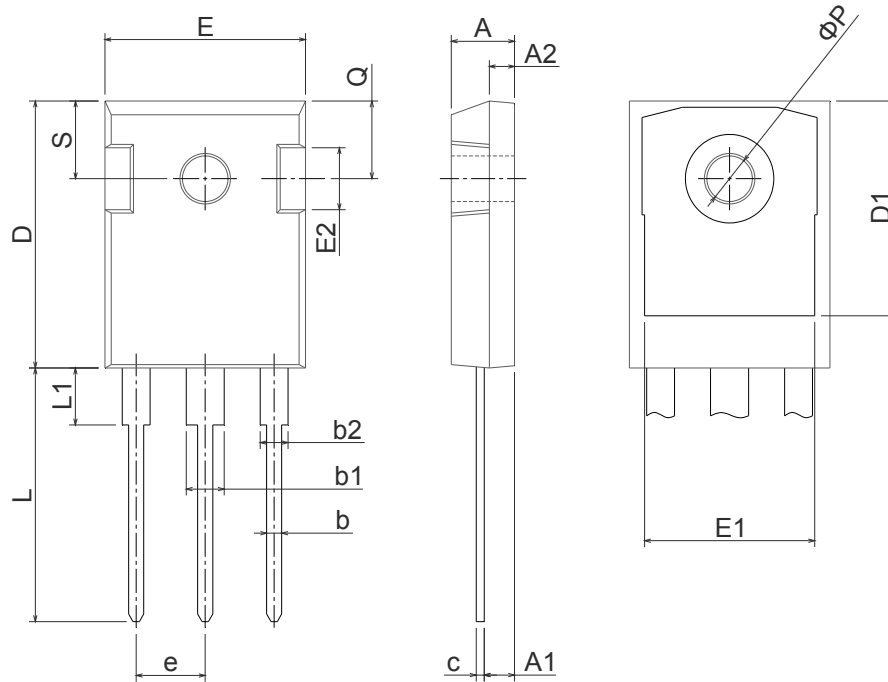


Fig.12 Single Pulse Maximum Power Dissipation

## Physical Dimension

## TO-247

Dimensions are in millimeters, unless otherwise specified



Dimension	Min(mm)	Max(mm)
A	4.70	5.31
A1	2.20	2.60
A2	1.50	2.49
b	0.99	1.40
b1	2.59	3.43
b2	1.65	2.39
c	0.38	0.89
D	20.30	21.46
D1	13.08	-
E	15.45	16.26
E1	13.06	14.02
E2	4.32	5.49
e	5.45BSC	
L	19.81	20.57
L1	-	4.50
ΦP	3.50	3.70
Q	5.38	6.20
S	6.15BSC	

**DISCLAIMER:**

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